

# BRD70N03

Rev.E Dec.-2017

## 描述 / Descriptions

TO-252 塑封封装 N 沟道 MOS 场效应管。N-CHANNEL MOSFET in a TO-252 Plastic Package.

## 特征 / Features

具有低导通电阻的超高密度设计，坚固可靠，表面贴装封装。

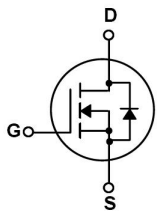
Super high dense cell design for low  $R_{DS(on)}$ , Rugged and reliable, surface mount package.

## 用途 / Applications

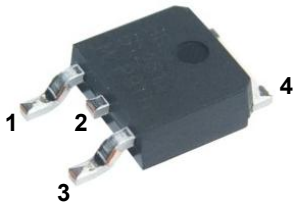
用于高功率 DC/DC 转换和功率开关。

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

## 内部等效电路 / Equivalent Circuit



## 引脚排列 / Pinning



PIN1 : G

PIN 2 : D

PIN 3 : S

PIN 4 : D

## 放大及印章代码 / $h_{FE}$ Classifications & Marking

见印章说明。 See Marking Instructions.

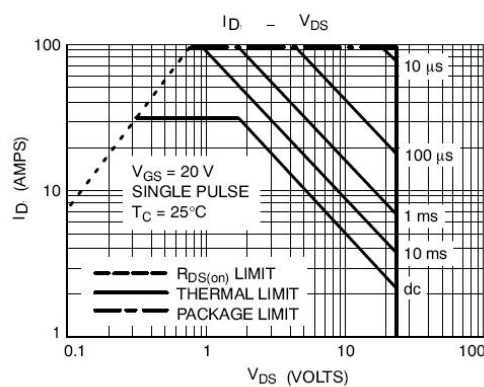
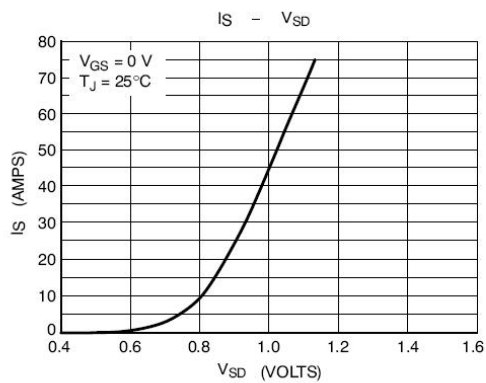
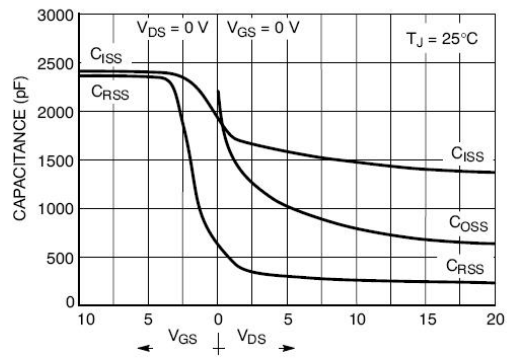
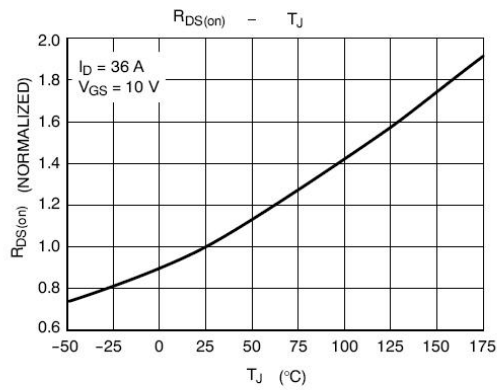
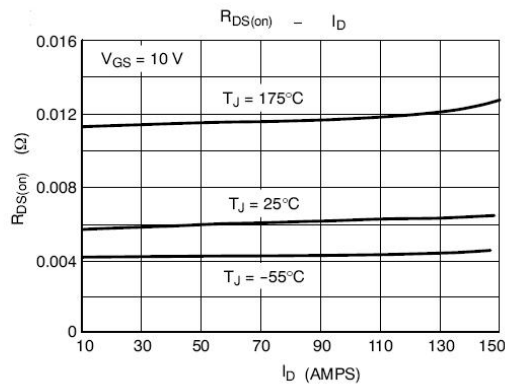
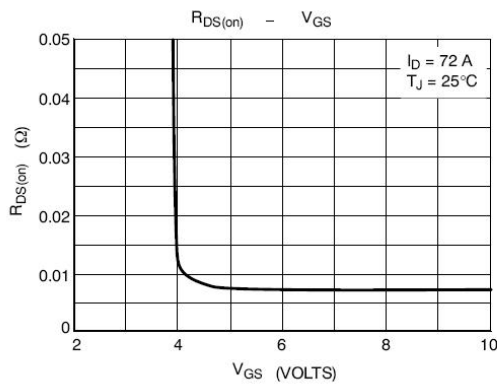
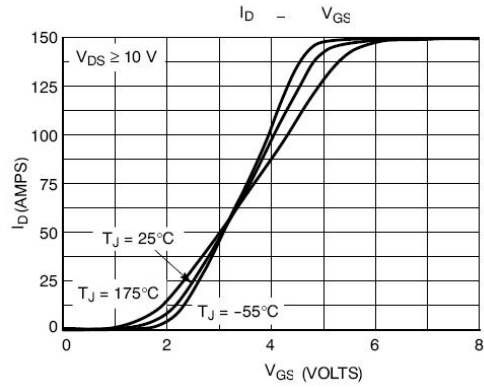
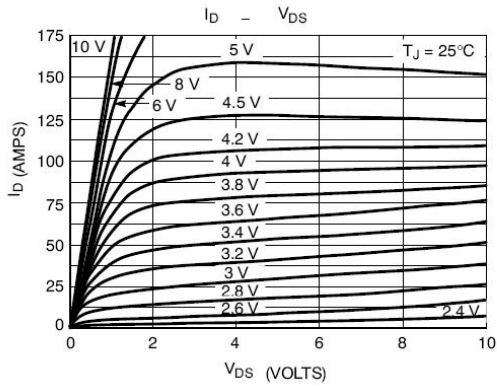
**极限参数 / Absolute Maximum Ratings(Ta=25°C)**

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	$V_{DSS}$	30	V
Drain Current	$I_D(T_c=25^\circ\text{C})$	62.8	A
Drain Current - Pulsed	$I_{DM}$	140	A
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Single Pulsed Avalanche Energy	$E_{AS}$	71.7	mJ
Power Dissipation	$P_D$	1.36	W
	$P_D(T_c=25^\circ\text{C})$	62.5	W
Junction-to-Ambient	$R_{\theta JA}$	110	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	$T_J, T_{stg}$	-55 to 150	$^\circ\text{C}$

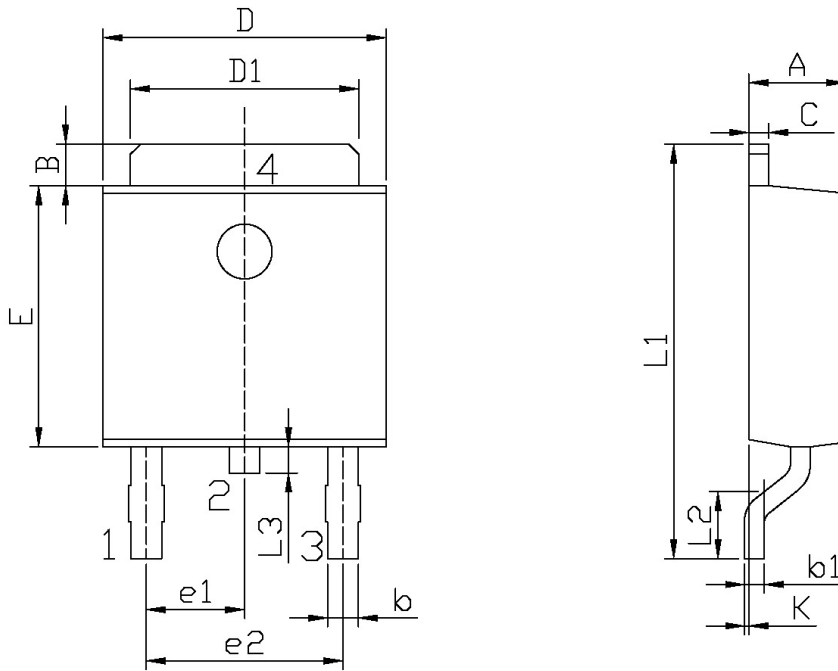
**电性能参数 / Electrical Characteristics(Ta=25°C)**

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V$ $I_D=250\mu A$	30			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=20V$ $V_{GS}=0V$			1.5	$\mu A$
Gate-Body Leakage Current Forward	$I_{GSS}$	$V_{GS}=\pm 20V$ $V_{DS}=0V$			$\pm 0.1$	$\mu A$
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	1.0	1.2	3.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=20A$		5.6	8.0	m $\Omega$
		$V_{GS}=4.5V$ $I_D=20A$		8.1	13	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=10V$ $I_D=15A$		27		S
Drain-Source Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V$ $I_S=20A$			1.2	V
Input Capacitance	$C_{iss}$	$V_{DS}=20V$ $V_{GS}=0V$ $f=1.0\text{MHz}$		1333		pF
Output Capacitance	$C_{oss}$			600		
Reverse Transfer Capacitance	$C_{rss}$			218		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=10V$ $I_D=36A$ $V_{GS}=10V$ $R_G=3.0\Omega$		6.9		ns
Turn-On Rise Time	$t_r$			1.3		
Turn-Off Delay Time	$t_{d(off)}$			18.4		
Turn-Off Fall Time	$t_f$			5.5		

**电参数曲线图 / Electrical Characteristic Curve**



外形尺寸图 / Package Dimensions

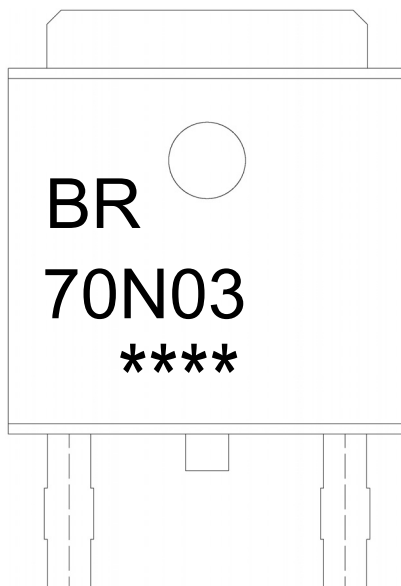


单位: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	2.20	2.40	E	5.95	6.25
B	0.95	1.25	e1	2.24	2.34
b	0.50	0.70	e2	4.43	4.73
b1	0.45	0.55	L1	9.45	9.95
C	0.45	0.55	L2	1.25	1.75
D	6.45	6.75	L3	0.60	0.90
D1	5.10	5.50	K	0.00	0.10

TO-252

**印章说明 / Marking Instructions**



说明：

BR： 为公司代码

70N03： 为型号代码

\*\*\*\*： 为生产批号代码，随生产批号变化

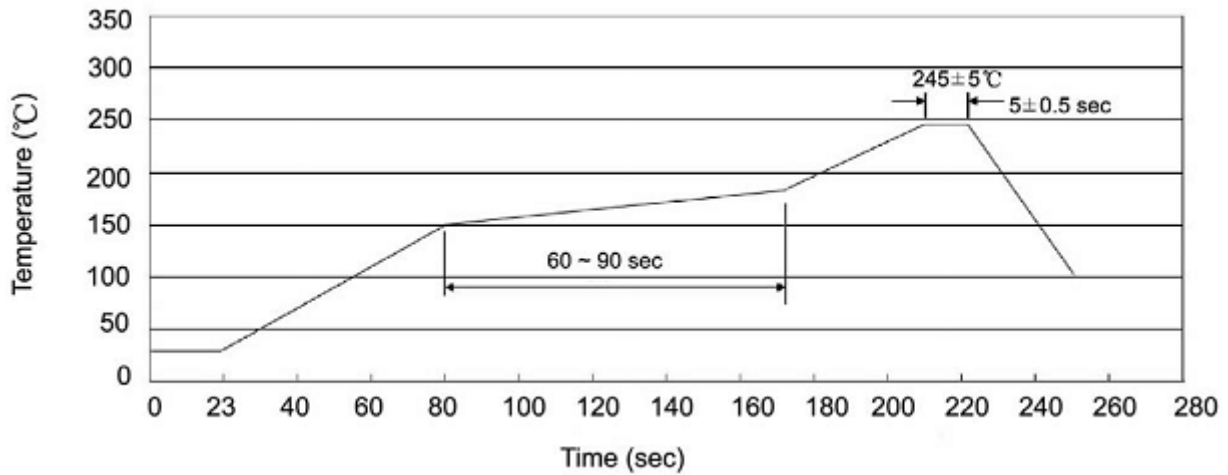
Note:

BR: Company Code.

70N03: Product Type Code.

\*\*\*\*: Lot No. Code, code change with Lot No.

**回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)**



说明：

- 1、预热温度 25~150°C，时间 60~90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:25~150°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

**耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions**

温度：260±5°C      时间：10±1 sec.      Temp.:260±5°C      Time:10±1 sec

**包装规格 / Packaging SPEC.**

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
TO-252	2,500	2	5,000	5	25,000	13" × 16	360×360×50	385×257×392

套管包装 / TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-251/252	75	48	3,600	5	18,000	526×20.5×5.25	555×164×50	575×290×180

**使用说明 / Notices**